

PROCEEDINGS OF SPIE

Gallium Nitride Materials and Devices XII

**Jen-Inn Chyi
Hiroshi Fujioka
Hadis Morkoç
Yasushi Nanishi
Ulrich T. Schwarz
Jong-In Shim**
Editors

**30 January–2 February 2017
San Francisco, California, United States**

Sponsored and Published by
SPIE

Volume 10104

Proceedings of SPIE 0277-786X, V. 10104

SPIE is an international society advancing an interdisciplinary approach to the science and application of light.

Gallium Nitride Materials and Devices XII, edited by Jen-Inn Chyi, Hiroshi Fujioka, Hadis Morkoç,
Yasushi Nanishi, Ulrich T. Schwarz, Jong-In Shim, Proc. of SPIE Vol. 10104, 1010401
© 2017 SPIE · CCC code: 0277-786X/17/\$18 · doi: 10.1117/12.2276185

Proc. of SPIE Vol. 10104 1010401-1

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Author(s), "Title of Paper," in *Gallium Nitride Materials and Devices XII*, edited by Jen-Inn Chyi, Hiroshi Fujioka, Hadis Morkoç, Yasushi Nanishi, Ulrich T. Schwarz, Jong-In Shim, Proceedings of SPIE Vol. 10104 (SPIE, Bellingham, WA, 2017) Seven-digit Article CID Number.

ISSN: 0277-786X

ISSN: 1996-756X (electronic)

ISBN: 9781510606494

ISBN: 9781510606500 (electronic)

Published by

SPIE

P.O. Box 10, Bellingham, Washington 98227-0010 USA

Telephone +1 360 676 3290 (Pacific Time) · Fax +1 360 647 1445

SPIE.org

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Printed in the United States of America.

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Contents

vii	Authors
ix	Conference Committee

GROWTH I

- 10104 03 **Recent progress of high-quality GaN substrates by HVPE method (Invited Paper)** [10104-2]

GROWTH II

- 10104 08 **Predicted lattice-misfit stresses in a gallium-nitride (GaN) film** [10104-7]

MATERIAL CHARACTERIZATION I

- 10104 09 **Carrier dynamics studies of III-nitride materials using photo-acoustic and photoluminescence measurements (Invited Paper)** [10104-8]

MATERIAL CHARACTERIZATION III

- 10104 01 **Design of Al-rich AlGaN quantum well structures for efficient UV emitters (Invited Paper)** [10104-16]

- 10104 0J **AlGaN-based metal-semiconductor-metal photodetectors with high external quantum efficiency at low operating voltage (Invited Paper)** [10104-17]

NANOSTRUCTURES AND DEVICES I

- 10104 0Q **Radiative recombination in polar, non-polar, and semi-polar III-nitride quantum wells** [10104-24]

NANOSTRUCTURES AND DEVICES II

- 10104 0U **Nanoscale characterization of GaN/InGaN multiple quantum wells on GaN nanorods by photoluminescence spectroscopy** [10104-28]

- 10104 0V **Health-friendly high-quality white light using violet-green-red laser and InGaN nanowires-based true yellow nanowires light-emitting diodes** [10104-29]

NANOSTRUCTURES AND DEVICES III

- 10104 13 **Electrically conductive ZnO/GaN distributed Bragg reflectors grown by hybrid plasma-assisted molecular beam epitaxy** [10104-37]

ELECTRON DEVICES I

- 10104 18 **Optimal III-nitride HEMTs: from materials and device design to compact model of the 2DEG charge density** [10104-42]

ELECTRON DEVICES II

- 10104 19 **GaN HEMTs with p-GaN gate: field- and time-dependent degradation (Invited Paper)** [10104-43]

- 10104 1B **Electrical characteristics of high-power AlGaN-GaN high electron mobility transistors irradiated with protons and heavy ions** [10104-45]

ELECTRON DEVICES III

- 10104 1E **Piezoelectric modulation of surface voltage in GaN and AlGaN/GaN: charge screening effects and 2DEG** [10104-48]

- 10104 1F **Investigation of GaN Fin-HEMTs with micron-scale fin width** [10104-49]

LASER DIODES

- 10104 1H **Recent improvement in nitride lasers (Invited Paper)** [10104-51]

- 10104 1J **Modeling of optical and electrical confinements in nitride VCSELs** [10104-53]

- 10104 1L **AlGaN laser-diode technology for optical clocks and atom interferometry** [10104-55]

LEDS I

- 10104 1R **Dominant transverse-electric polarized emission from 298 nm MBE-grown AlN-delta-GaN quantum well ultraviolet light-emitting diodes** [10104-60]

LEDS II

- 10104 1U **Semipolar InGaN-based superluminescent diodes for solid-state lighting and visible light communications** [10104-63]

- 10104 1X **Gallium nitride light sources for optical coherence tomography** [10104-66]

LEDS III

- 10104 1Y **InGaN-based flexible light emitting diodes (Invited Paper)** [10104-67]
- 10104 22 **Processing and characterization of high resolution GaN/InGaN LED arrays at 10 micron pitch for micro display applications** [10104-71]

Authors

Numbers in the index correspond to the last two digits of the seven-digit citation identifier (CID) article numbering system used in Proceedings of SPIE. The first five digits reflect the volume number. Base 36 numbering is employed for the last two digits and indicates the order of articles within the volume. Numbers start with 00, 01, 02, 03, 04, 05, 06, 07, 08, 09, 0A, 0B...0Z, followed by 10-1Z, 20-2Z, etc.

- Adolph, David, 13
Alyamani, Ahmed Y., 1U
Anjum, Dalaver H., 0V
Aventurier, Bernard, 22
Bartholomeus, J., 19
Bayram, C., 1Y
Bonsall, Jeremy, 1B
Bremers, Heiko, 0Q
Brendel, M., 0J
Brodie, Miles, 1B
Brunner, F., 0J
Canato, E., 19
Carson, C., 1L
Chang, Li-Cheng, 1F
Chen, Weijian, 0U
Childs, David T. D., 1X
Christiansen, Silke, 0U
Conibeer, Gavin, 0U
Consiglio, Giuseppe Bernardo, 0V
Czernecki, R., 1L
Daami, Anis, 22
De Santi, C., 19
Denbaars, Steven P., 1U
Dupré, Ludovic, 22
El-Desouki, Munir M., 1U
Fujikura, Hajime, 03
Fukada, Haruki, 09
Funato, Mitsuru, 0I
Goldberg, Graham R., 1X
Groom, Kristian M., 1X
Haglund, Åsa, 13
Hangleiter, Andreas, 0Q
Hashemi, Ehsan, 13
Henning, Philipp, 0Q
Henry, Franck, 22
Hillard, Bob, 1E
Hjort, Filip, 13
Hogg, Richard A., 1X
Horenburg, Philipp, 0Q
Huang, Shujuan, 0U
Ichikawa, Shuhei, 0I
Islam, S. M., 1R
Ivanov, Pavlo, 1X
Ive, Tommy, 13
Janjua, Bilal, 0V
Jena, Debdeep, 1R
Jiang, Yi-Hong, 1F
Kanitani, Yuya, 09
Kasahara, Daiji, 1H
Kawakami, Yoichi, 0I
Kennedy, Kenneth L., 1X
Ketzer, Fedor Alexej, 0Q
Knigge, A., 0J
Korn, Ernst Ronald, 0Q
Kumamoto, Kyosuke, 0I
Lagowski, Jacek, 1E
Langer, Torsten, 0Q
Latzel, Michael, 0U
Lee, Changmin, 1U
Leonard, John T., 1U
Łęszczyński, M., 1L
Li, Kexin, 18
Lingley, Zachary, 1B
Liu, Cheng, 1R
Marona, L., 1L
Marra, Marjorie, 22
Mason, Maribeth, 1B
Masui, Shingo, 1H
McKnight, L. J., 1L
Meneghesso, G., 19
Meneghini, M., 19
Nagahama, Shin-ichi, 1H
Najda, S. P., 1L
Nakamura, Shuji, 1U
Nakano, Takashi, 09
Nakatsu, Yoshitaka, 1H
Ng, Tien Khee, 0V, 1U
Olivier, François, 22
Ooi, Boon S., 0V, 1U
Ooi, Yu Kee, 1R
Otoki, Yohei, 03
Ozaki, Nobuhiko, 1X
Patterson, Robert, 0U
Perlin, P., 1L
Prabaswara, Aditya, 0V
Rakheja, Shaloo, 18
Rossetto, I., 19
Rossow, Uwe, 0Q
Sakai, Shigeta, 09
Sarzata, R. P., 1J
Savtchouk, Alexandre, 1E
Schrayer, Bret, 1E
Shen, Chao, 0V, 1U
Shibata, Masatomo, 03
Shrestha, Santosh, 0U
Sin, Yongkun, 1B
Sokół, A. K., 1J
Speck, James S., 1U

Śpiewak, P., 1J
Stanczyk, S., 1L
Stothard, D., 1L
Suhir, E., 08
Suski, T., 1L
Targowski, G., 1L
Templier, François, 22
Tirano, Sauveur, 22
Tomiya, Shigetaka, 09
Trivellin, N., 19
Verney, Valentin, 22
Wasiak, M., 1J
Wen, Xiaoming, 0U
Weyers, M., 0J
Wilson, Marshall, 1E
Wisniewski, P., 1L
Wu, Chao-Hsin, 1F
Xing, Huili Grace, 1R
Yamaguchi, Atsushi A., 09
Yang, Jianfeng, 0U
Yang, Ming, 1F
Yi, S., 08
Yoshida, Takehiro, 03
Zanoni, E., 19
Zhang, Jing, 1R
Zhao, Chao, 0V

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Hadis Morkoç, Virginia Commonwealth University (United States)
- 2 Growth II
Hadis Morkoç, Virginia Commonwealth University (United States)
- 3 Material Characterization I
Michał Boćkowski, Institute of High Pressure Physics (Poland)
- 4 Material Characterization II
Jürgen H. Christen, Otto-von-Guericke-Universität Magdeburg
(Germany)
- 5 Material Characterization III
Eva Monroy, CEA Grenoble (France)
- 6 Nanostructures and Devices I
Raphaël Butté, Ecole Polytechnique Fédérale de Lausanne
(Switzerland)
- 7 Nanostructures and Devices II
Frank Bertram, Otto-von-Guericke-Universität Magdeburg (Germany)
- 8 Nanostructures and Devices III
Hiroshi Fujioka, The University of Tokyo (Japan)
- 9 Electron Devices I
Yasushi Nanishi, Ritsumeikan University (Japan)
- 10 Electron Devices II
Jen-Inn Chyi, National Central University (Taiwan)

- 11 Electron Devices III
Gaudenzio Meneghesso, Università degli Studi di Padova (Italy)
- 12 Laser Diodes
Russell D. Dupuis, Georgia Institute of Technology (United States)
- 13 LEDs I
Jong-In Shim, Hanyang University (Korea, Republic of)
- 14 LEDs II
Can Bayram, University of Illinois at Urbana-Champaign
(United States)
- 15 LEDs III
Hadis Morkoç, Virginia Commonwealth University (United States)

